



FORM 610-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Attorney Docket No.: 108-18.1	Application No.: 10/777,560
		Applicant: Harry S. Luan, et al.	
		Filing Date: February 11, 2004	Group:

Reference Designation		U.S. PATENT DOCUMENTS				Page 1
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
7/11 AA	6,204,139	3/20/01	Liu et al	438	385	—
7/11 AB	6,531,371	3/11/03	Hsu et al	438	385	—
AC						
AD						
AE						
AF						
AG						
AH						
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AJ						
AK						
AL						
AM						
AN						
AO						

#### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)

#### OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

7/11 AP	Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)," IEEE 2002.
7/11 AQ	Liu et al., "A New Concept for Non-Volatile Memory: The Electric Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films,"
7/11 AR	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films," American Institute of Physics, 2000, pg. 2749-2751.
AS	
AT	
AU	
AV	
AW	
AX	

EXAMINER *[Signature]* DATE CONSIDERED *3/26/2006*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.